				ATTY. DOCKET NO.:		APPLICATION NO.:			
LIS	T OF	REFERENCES CIT		4717-11500		10/716,451			
Form PTO-1449 (Use several sheets if necessary)					APPLICANT:				
					Fabrice LETERTRE				
					November 20, 2003 1765				
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*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS		PRIATE
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*EXAMINI	M ER:	Initial if reference conside	red, whether or	not citation is in	conformance with MPEP 60	9. Draw line	through cita	tion if	not in
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